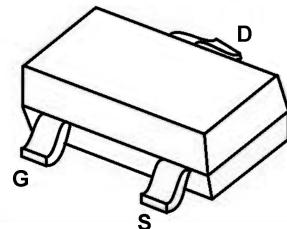


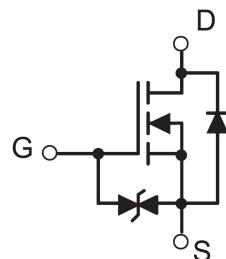
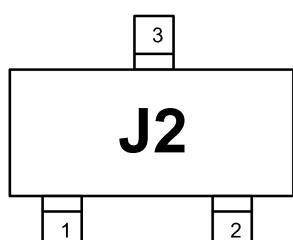
60V N-Channel MOSFET

FEATURE

- We declare that the material of product compliance with RoHS requirements and Halogen Free
- Low threshold voltage,makes it ideal for low voltage applications
- ESD Protected
- $R_{DS(ON)} \leq 3\Omega$ @ $V_{GS}=10V$
 $R_{DS(ON)} \leq 4\Omega$ @ $V_{GS}=4.5V$

SOT-323**APPLICATION**

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

CIRCUIT DIAGRAM**MARKING**

J2 =Device Code

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.22	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

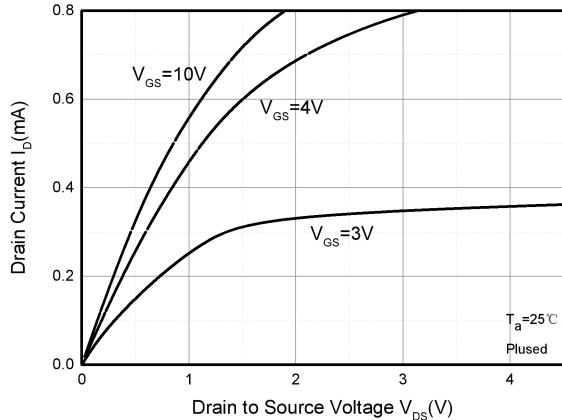
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	60	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$	-	-	1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 5	μA
Gate threshold voltage ¹⁾	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.8	1	1.45	V
Drain-source on-resistance ¹⁾	$R_{DS(\text{on})}$	$V_{GS} = 10V, I_D = 500\text{mA}$	-	1.5	3	Ω
Dynamic characteristics²⁾						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	-	27	-	pF
Output Capacitance	C_{oss}		-	13	-	
Reverse Transfer Capacitance	C_{rss}		-	6	-	
Switching Characteristics¹⁾²⁾						
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30V, I_D=0.29A, V_{GS}=10V, R_G=6\Omega$	-	-	5	nS
Rise time	tr		-	-	18	
Turn-off delay time	$t_{d(off)}$		-	-	36	
Fall time	tf		-	-	14	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	$V_{GS}=0V, I_S=500\text{mA}$	0.5	-	1.4	V

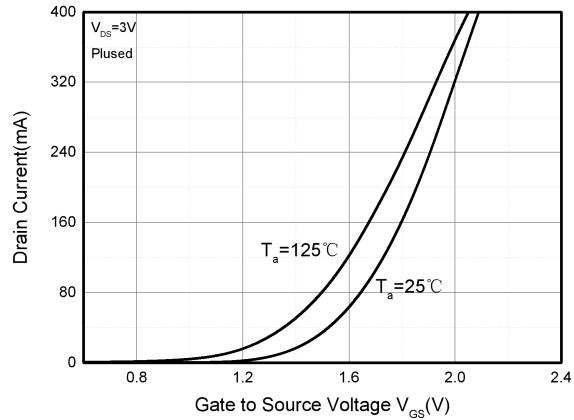
Notes:

- 1) Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- 2) These parameters have no way to verify.

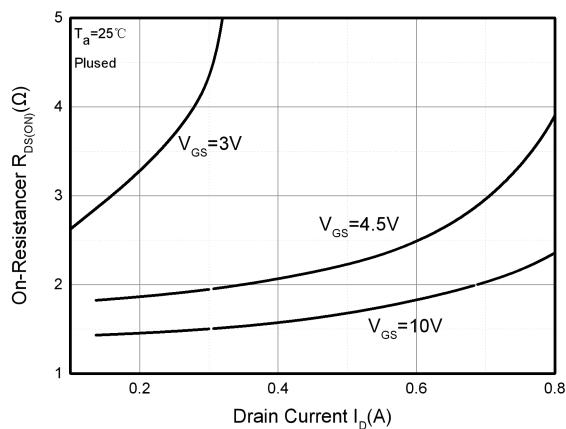
TYPICAL CHARACTERISTIC



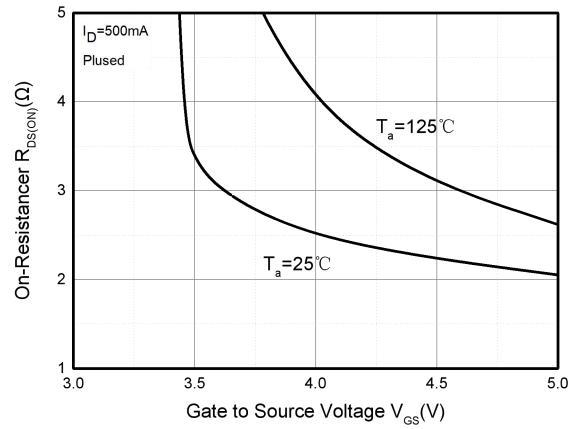
Output Characteristics



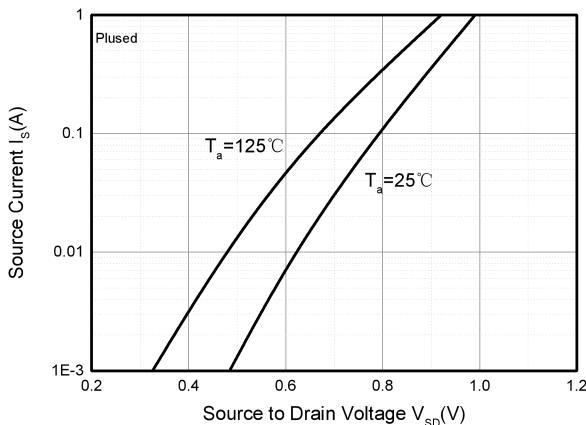
Transfer Characteristics



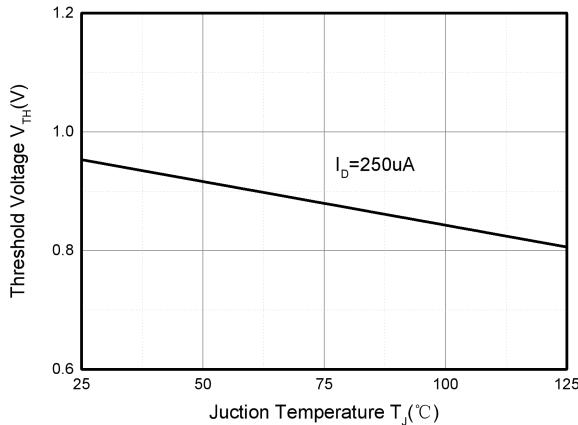
RDS(ON) — ID



RDS(ON) — VGS

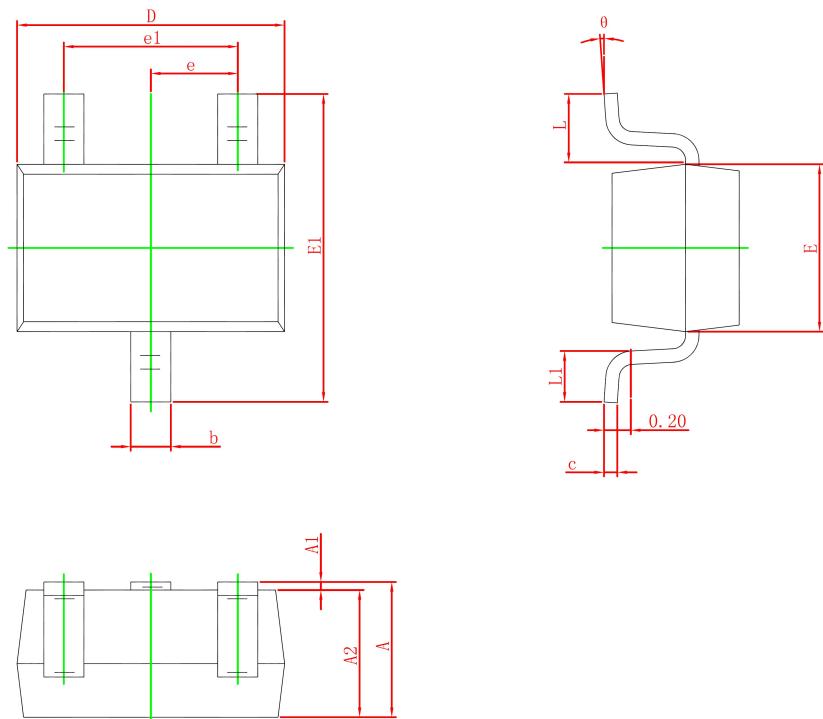


IS — VSD



Threshold Voltage

SOT-323 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°